



**DACO SEMICONDUCTOR CO., LTD.**

**MBR400150CT(R)**  
**THRU**  
**MBR400200CT(R)**

## SCHOTTKY DIODE MODULE TYPES 400A

### Features

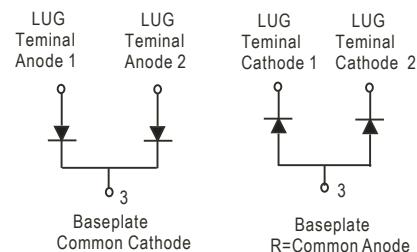
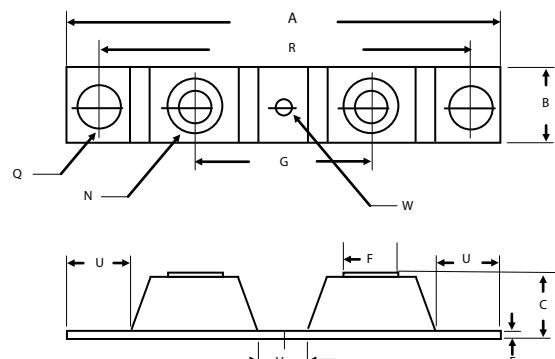
High Surge Capability  
Types Up to 200V V<sub>RRM</sub>

**400Amp Rectifier**  
**150-200 Volts**

### Maximum Ratings

Operating Temperature: -55 °C to +150 °C  
Storage Temperature: -55 °C to +150 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBR400150CT(R)	150V	106V	150V
MBR400200CT(R)	200V	141V	200V



### Electrical Characteristics @ 25 °C Unless Otherwise Specified

Average Forward Current (Per pkg)	I <sub>F(AV)</sub>	400A	TC=125°C
Peak Forward Surge Current (Per leg)	I <sub>FSM</sub>	3000A	8.3ms, half sine
Maximum Instantaneous Forward Voltage (Per leg)	V <sub>F</sub>	150V 200V	0.88V 0.92V
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg)	I <sub>R</sub>	3mA 10mA 50mA	TJ = 25 °C TJ = 100 °C TJ = 150 °C
Maximum Thermal Resistance Junction To Case (Per leg)	R <sub>θ j c</sub>	0.35 °C/W	

#### NOTE :

(1) Pulse Test: Pulse Width 300 μ sec. Duty Cycle < 2%

DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	-----	3.630	-----	92.40
B	0.700	0.800	17.78	20.32
C	-----	0.650	-----	16.51
E	0.130	0.141	3.30	3.60
F	0.482	0.490	12.25	12.45
G	1.368	BSC	34.75	BSC
N	1/4-20 UNC FULL			
Q	0.275	0.290	6.99	7.37
R	3.150	BSC	80.01	BSC
U	0.600	-----	15.24	-----
V	0.312	0.370	7.92	9.40
W	0.180	0.195	4.57	4.95



DACO SEMICONDUCTOR CO., LTD.

MBR400150CT(R)

THRU  
MBR400200CT(R)

Figure .1-Typical Forward Characteristics

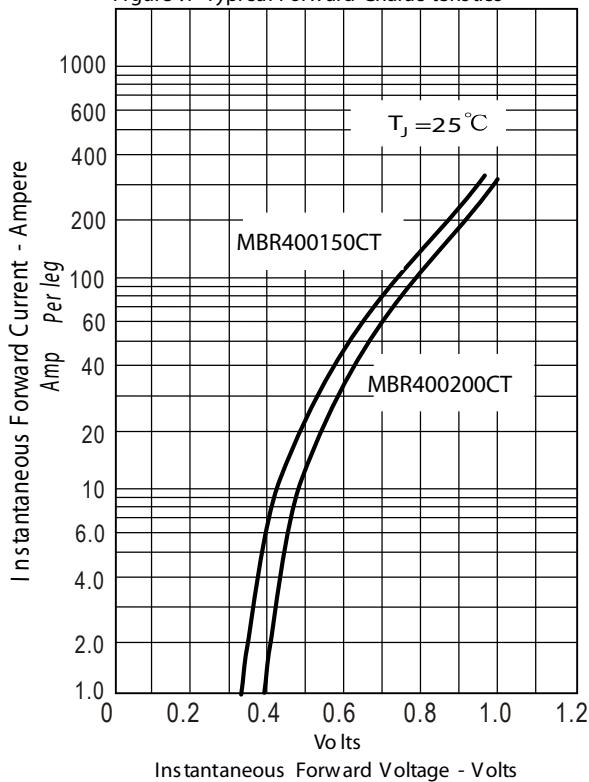


Figure .2- Forward Derating Curve

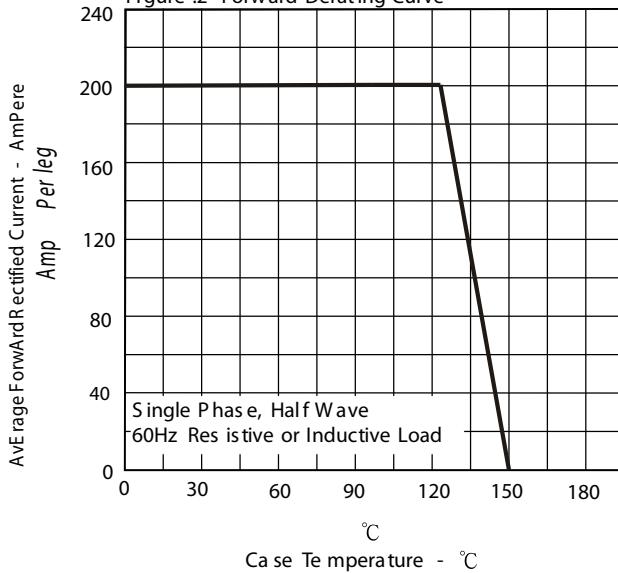


Figure .4- Typical Reverse Characteristics

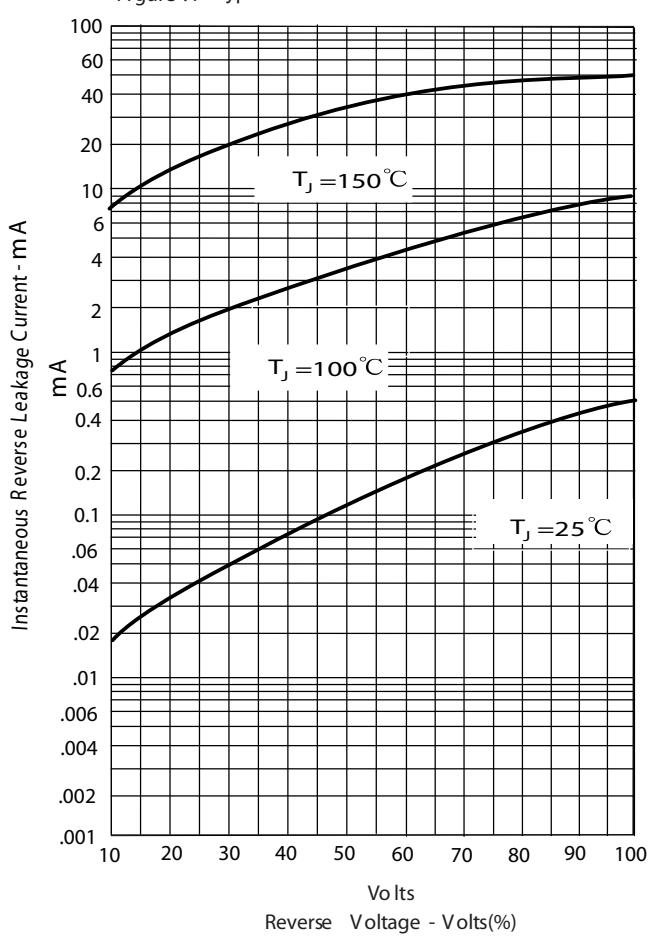


Figure .3- Peak Forward Surge Current

